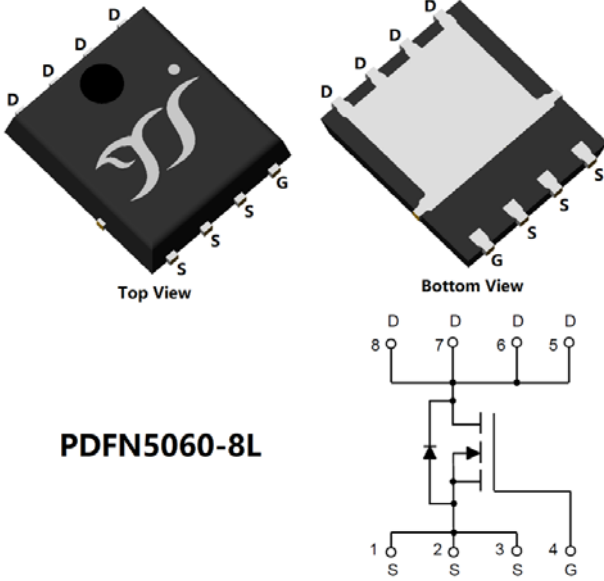


## N-Channel Enhancement Mode Field Effect Transistor



### Product Summary

- $V_{DS}$  60V
- $I_D$  30A
- $R_{DS(ON)}$ ( at  $V_{GS}=10V$ )  $<21m\Omega$
- $R_{DS(ON)}$ ( at  $V_{GS}=4.5V$ )  $<26m\Omega$
- 100% EAS Tested
- 100%  $\nabla V_{DS}$  Tested

### General Description

- Excellent package for heat dissipation
- High density cell design for low  $R_{DS(ON)}$
- Moisture Sensitivity Level 3
- Part no. with suffix "Q" means AEC-Q101 qualified

### Applications

- Power switching application
- Uninterruptible power supply
- DC-DC convertor
- 12V and 24V Automotive systems

### ■ Absolute Maximum Ratings ( $T_A=25^\circ C$ unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-source Voltage		$V_{DS}$	60	V
Gate-source Voltage		$V_{GS}$	$\pm 20$	V
Drain Current	$T_A=25^\circ C$	$I_D$	7.3	A
	$T_A=100^\circ C$		4.7	
	$T_C=25^\circ C$		30	
	$T_C=100^\circ C$		19	
Pulsed Drain Current <sup>A</sup>		$I_{DM}$	120	A
Avalanche energy <sup>B</sup>		EAS	90	mJ
Total Power Dissipation <sup>C</sup>	$T_A=25^\circ C$	$P_D$	2.5	W
	$T_A=100^\circ C$		1	
	$T_C=25^\circ C$		44.5	
	$T_C=100^\circ C$		17.8	
Thermal Resistance Junction-to-Case		$R_{\theta JC}$	2.8	$^\circ C/W$
Thermal Resistance Junction-to-Ambient <sup>D</sup>		$R_{\theta JA}$	50	$^\circ C/W$
Junction and Storage Temperature Range		$T_J, T_{STG}$	-55~+150	$^\circ C$

### ■ Ordering Information (Example)

PREFERRED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
YJG30N06AQ	F1	YJG30N06A	5000	10000	100000	13" reel



# YJG30N06AQ

## ■ Electrical Characteristics (T<sub>J</sub>=25°C unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
<b>Static Parameter</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> = 0V, I <sub>D</sub> =250μA	60			V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =60V, V <sub>GS</sub> =0V			1	μA
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V			±100	nA
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> =250μA	1	1.5	2.5	V
Static Drain-Source On-Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =15A		16	21	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =10A		17	26	mΩ
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =15A, V <sub>GS</sub> =0V		0.85	1.2	V
Gate resistance	R <sub>G</sub>	f=1MHz		1		Ω
<b>Dynamic Parameters</b>						
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =25V, V <sub>GS</sub> =0V, f=1MHz		2450		pF
Output Capacitance	C <sub>oss</sub>			165		
Reverse Transfer Capacitance	C <sub>riss</sub>			125		
<b>Switching Parameters</b>						
Total Gate Charge	Q <sub>g</sub>	V <sub>GS</sub> =10V, V <sub>DS</sub> =30V, I <sub>D</sub> =20A	-	46	-	nC
Gate-Source Charge	Q <sub>gs</sub>		-	6	-	
Gate-Drain Charge	Q <sub>gd</sub>		-	11	-	
Reverse Recovery Charge	Q <sub>rr</sub>	I <sub>F</sub> =20A, di/dt=100A/us	-	28.2	-	nC
Reverse Recovery Time	t <sub>rr</sub>		-	32	-	ns
Turn-on Delay Time	t <sub>D(on)</sub>	V <sub>GS</sub> =10V, V <sub>DD</sub> =30V, I <sub>D</sub> =20A	-	9	-	ns
Turn-on Rise Time	t <sub>r</sub>		-	41	-	
Turn-off Delay Time	t <sub>D(off)</sub>		-	28	-	
Turn-off fall Time	t <sub>f</sub>		-	2.8	-	

A. Repetitive rating; pulse width limited by max. junction temperature.

B. T<sub>J</sub>=25°C, V<sub>DD</sub>=40V, V<sub>G</sub>=10V, L=0.5mH, I<sub>AS</sub>=19A.

C. P<sub>q</sub> is based on max. junction temperature, using junction-case thermal resistance.

D. The value of R<sub>θJA</sub> is measured with the device mounted on 1 in<sup>2</sup> FR-4 board with 2oz. Copper, in the still air environment with T<sub>A</sub>=25°C. The maximum allowed junction temperature of 150°C. The value in any given application depends on the user's specific board design.



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## Typical Electrical and Thermal Characteristics Diagrams

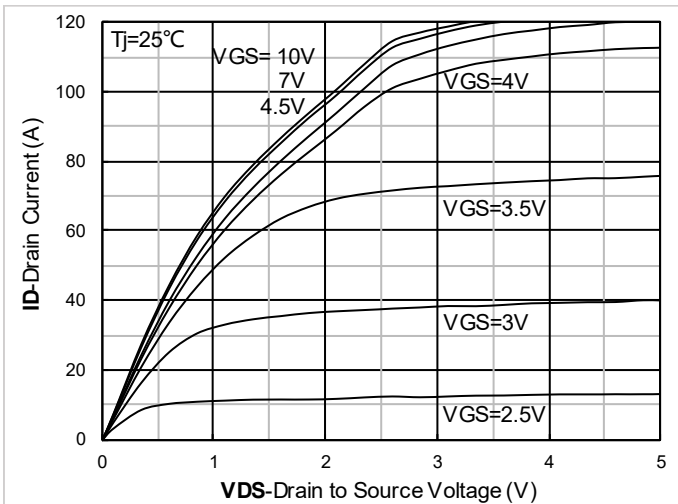


Figure 1. Output Characteristics

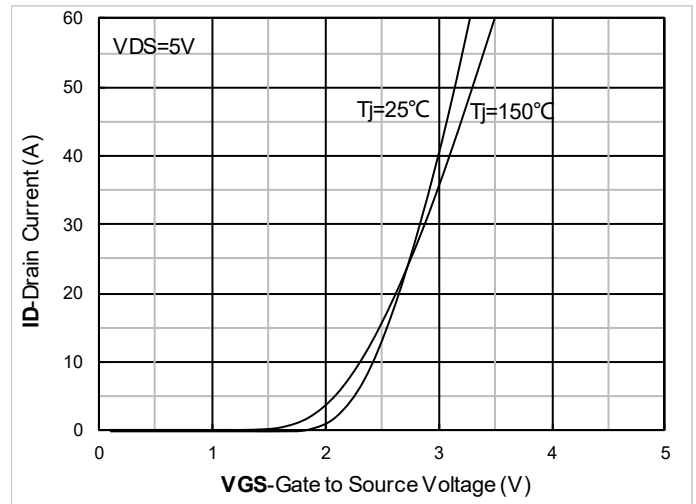


Figure 2. Transfer Characteristics

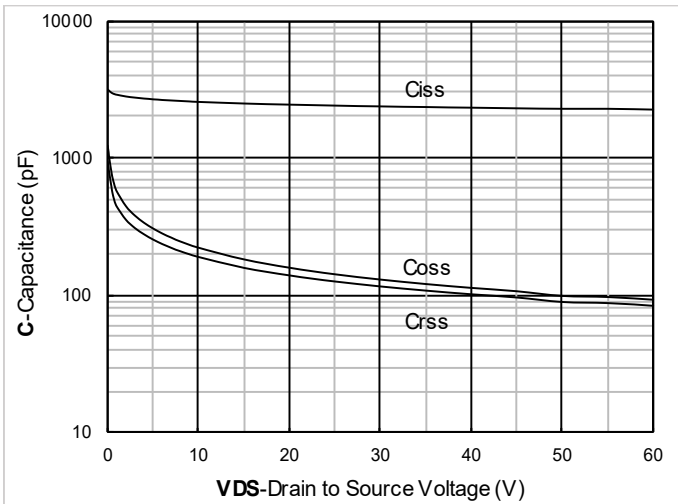


Figure 3. Capacitance Characteristics

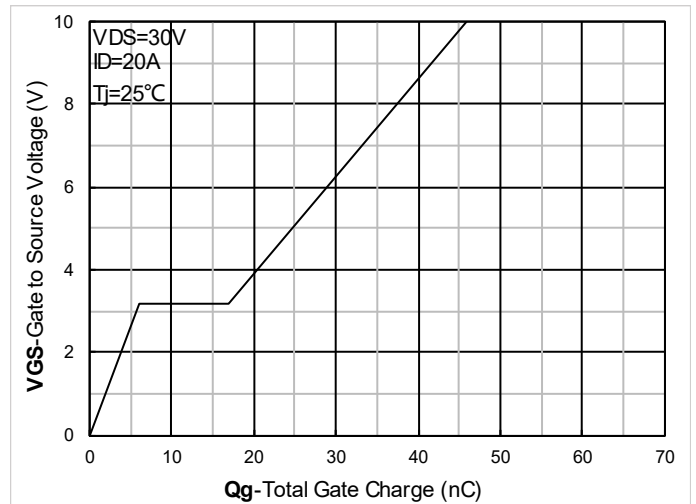


Figure 4. Gate Charge

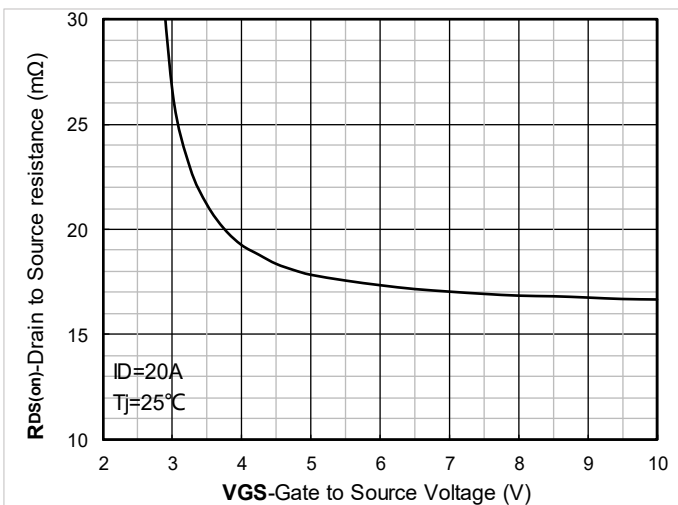


Figure 5. On-Resistance vs Gate to Source Voltage

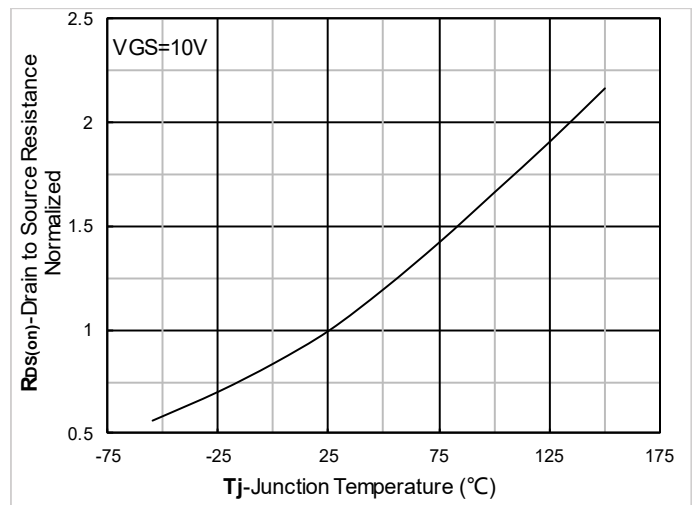


Figure 6. Normalized On-Resistance



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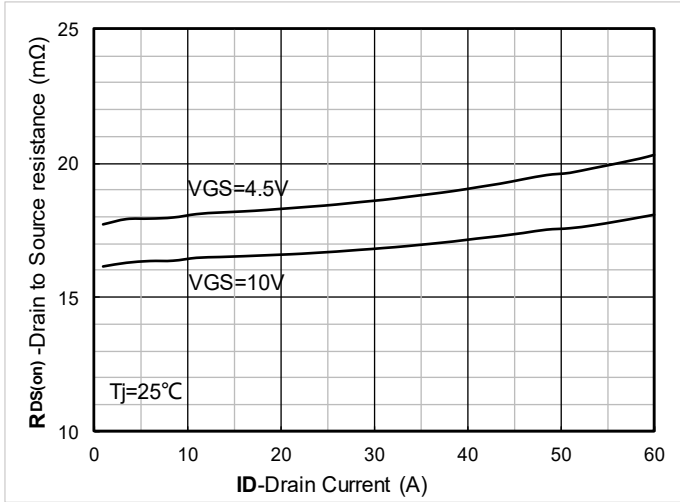


Figure 7. RDS(on) VS Drain Current

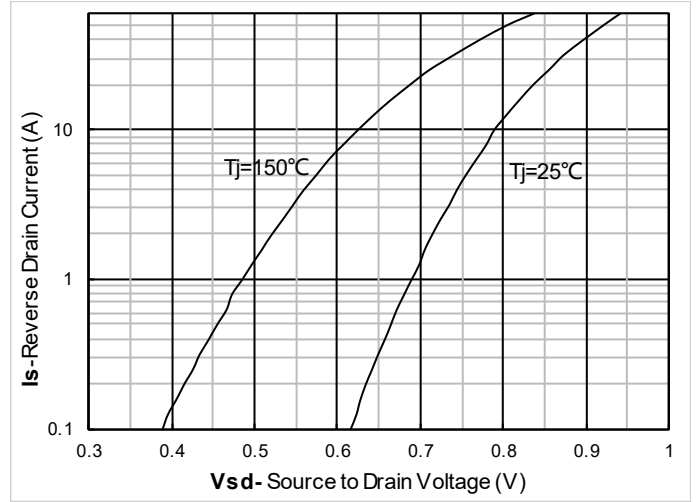


Figure 8. Forward characteristics of reverse diode

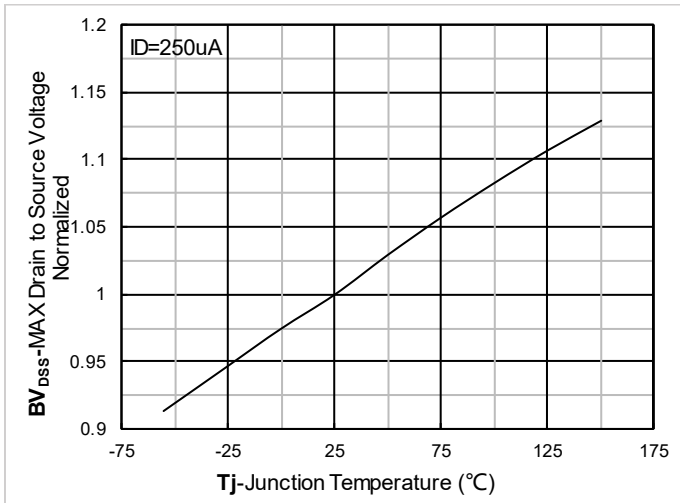


Figure 9. Normalized breakdown voltage

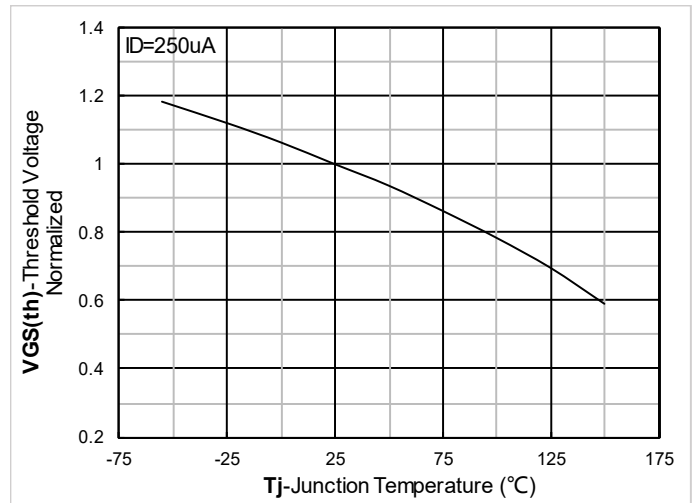


Figure 10. Normalized Threshold voltage

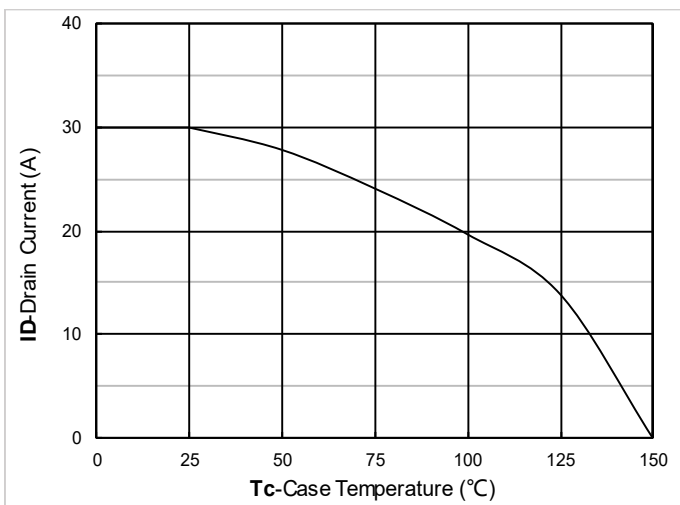


Figure 11. Current dissipation

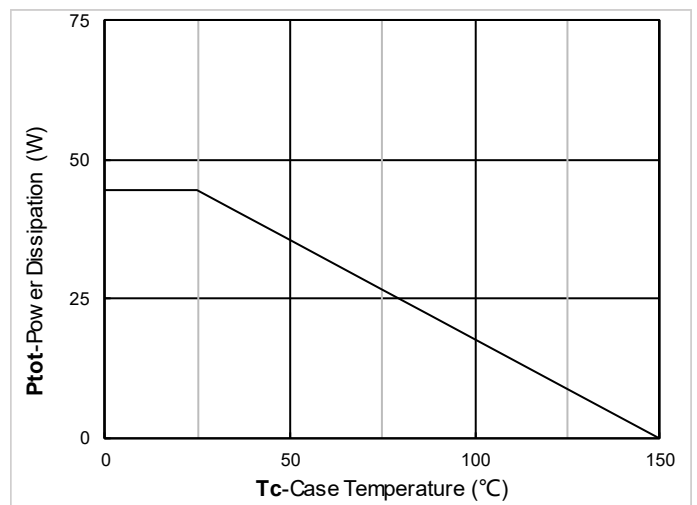


Figure 12. Power dissipation



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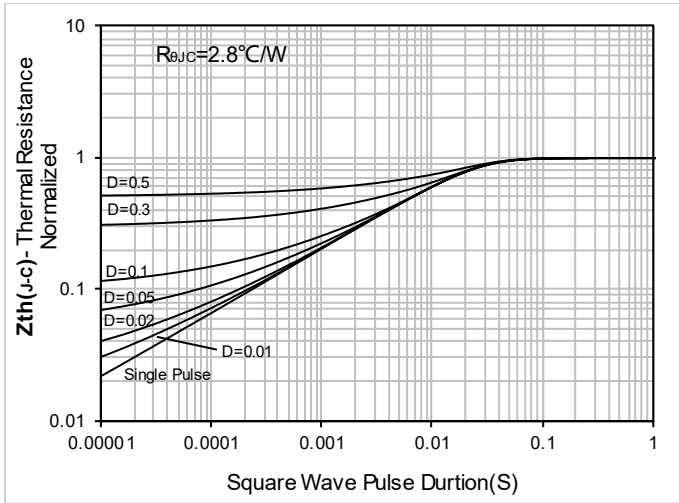


Figure 13. Maximum Transient Thermal Impedance

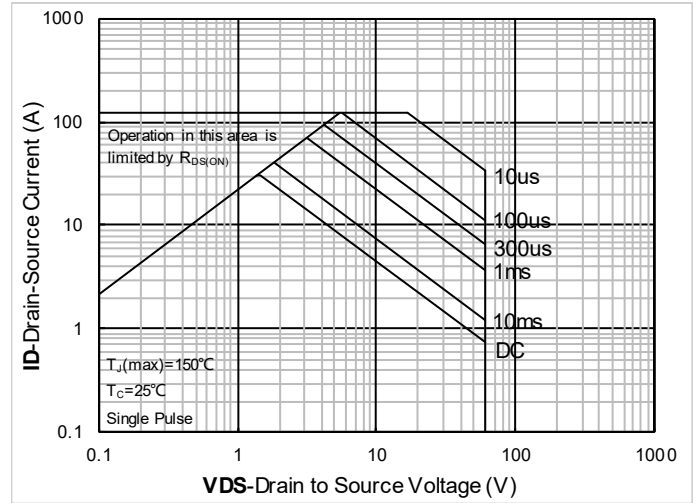
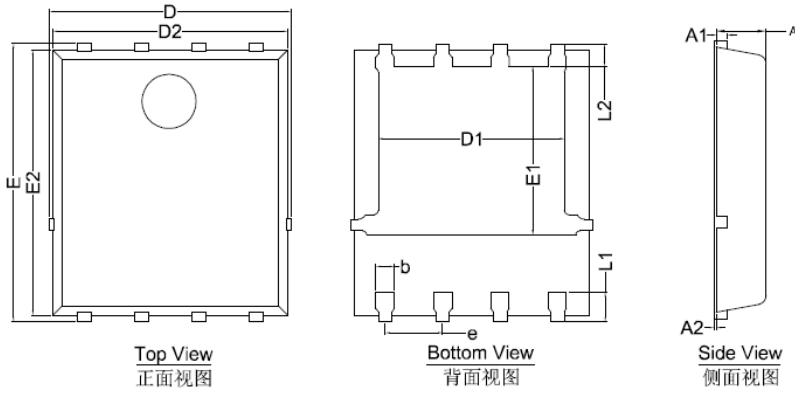


Figure 14. Safe Operation Area

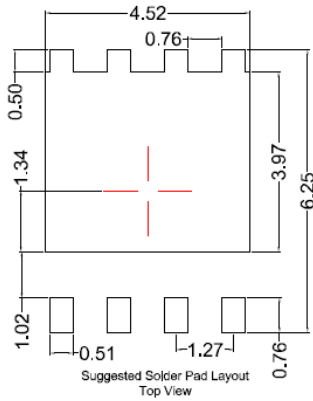


# YJG30N06AQ

## ■ PDFN5060-8L-1.1MM Package information



SYMBOL	MILLIMETER		
	MIN	NOM	MAX
D	5.15	5.35	5.55
E	5.95	6.15	6.35
A	1.00	1.10	1.20
A1	0.254 BSC		
A2			0.10
D1	3.92	4.12	4.32
E1	3.52	3.72	3.92
D2	5.00	5.20	5.40
E2	5.66	5.86	6.06
L1	0.56	0.66	0.76
L2	0.50 BSC		
b	0.31	0.41	0.51
e	1.27 BSC		



Note:  
 1. Controlling dimension: in millimeters.  
 2. General tolerance:  $\pm 0.10$ mm.  
 3. The pad layout is for reference purposes only.



## YJG30N06AQ

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